



Features

- High isolation 3750 V_{RMS}
- DC input with transistor output
- Operating temperature range - 55 °C to 110 °C
- Green Package
- Regulatory Approvals
 - UL - UL1577 (E364000)
 - VDE - EN60747-5-5(VDE0884-5)
 - CQC – GB4943.1, GB8898
 - IEC60065, IEC60950

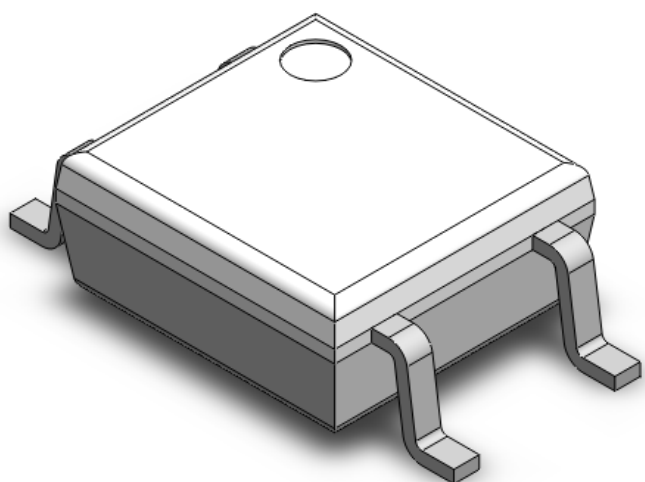
Description

The CT415 series consists of a photodarlington transistor optically coupled to a gallium arsenide Infrared-emitting diode in a 4-lead Mini-Flat package.

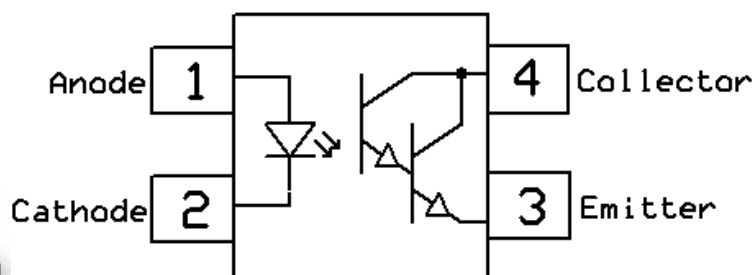
Applications

- Power supply regulators
- Digital logic outputs
- Microprocessor inputs

Package Outline



Schematic



**Absolute Maximum Rating at 25°C**

Symbol	Parameters	Ratings	Units	Notes
V _{ISO}	Isolation voltage	3750	V _{RMS}	
T _{OPR}	Operating temperature	-55 ~ +110	°C	
T _{STG}	Storage temperature	-55 ~ +150	°C	
T _{SOL}	Soldering temperature	260	°C	
P _{TOT}	Total power dissipation	170	mW	
Emitter				
I _F	Forward current	50	mA	
I _{F(TRANS)}	Peak transient current (≤1μs P.W,300pps)	1	A	
V _R	Reverse voltage	6	V	
P _D	Power dissipation	70	mW	
Detector				
P _D	Power dissipation	150	mW	
B _{VCEO}	Collector-Emitter Breakdown Voltage	60	V	
B _{VECO}	Emitter-Collector Breakdown Voltage	7	V	
I _C	Collector Current	80	mA	

**Electrical Characteristics** $T_A = 25^\circ\text{C}$ (unless otherwise specified)**Emitter Characteristics**

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
V_F	Forward voltage	$I_F = 10\text{mA}$		1.4	1.6	V	
I_R	Reverse Current	$V_R = 6\text{V}$	-	-	5	μA	
C_{IN}	Input Capacitance	$f = 1\text{MHz}$	-	30	250	pF	

Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$B_{V_{CEO}}$	Collector-Emitter Breakdown	$I_C = 100\mu\text{A}$	35	-	-	V	
$B_{V_{ECO}}$	Emitter-Collector Breakdown	$I_E = 100\mu\text{A}$	7	-	-	V	
I_{CEO}	Collector-Emitter Dark Current	$V_{CE} = 10\text{V}, I_F = 0\text{mA}$	-	-	1	μA	

Transfer Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes	
CTR	Current Transfer Ratio	$I_F = 1\text{mA}, V_{CE} = 2\text{V}$	CT415	600	-	-	%	
			CT415A	3000	-	6500		
			CT415B	5500	-	-		
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$I_F = 20\text{mA}, I_C = 5\text{mA}$	-	0.8	1	V		
R_{IO}	Isolation Resistance	$V_{IO} = 500\text{V}_{DC}$	5×10^{10}					
C_{IO}	Isolation Capacitance	$f = 1\text{MHz}$		0.5	1	pF		

Switching Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
t_r	Rise Time	$I_C = 10\text{mA}, V_{CE} = 2\text{V}, R_L = 100$	-	-	300	μs	
t_f	Fall Time		-	-	250		



Typical Characteristic Curves

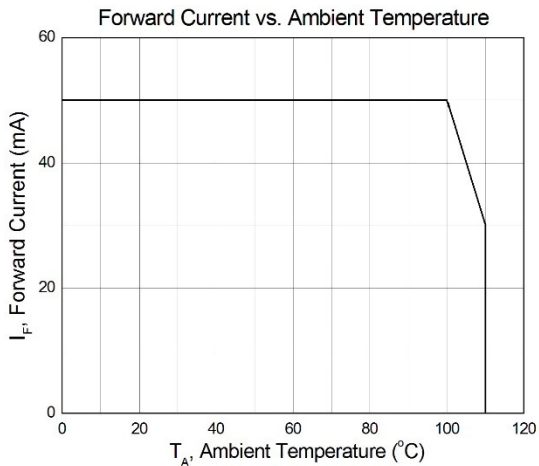


Figure 1

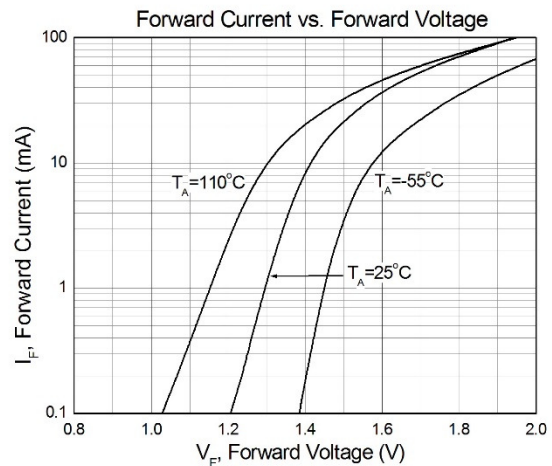


Figure 2

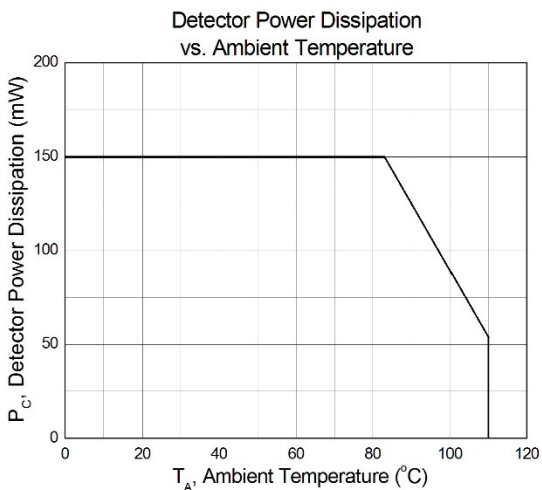


Figure 3

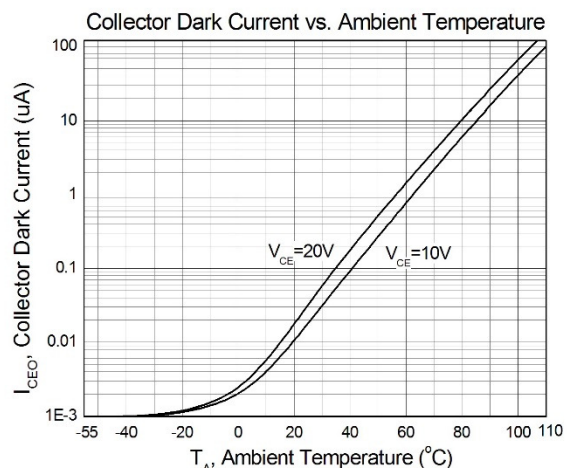


Figure 4

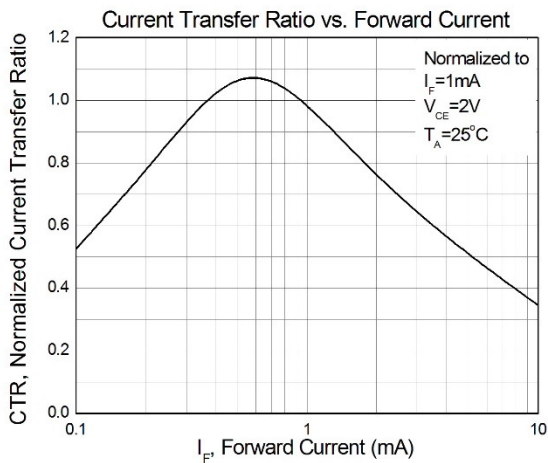


Figure 5

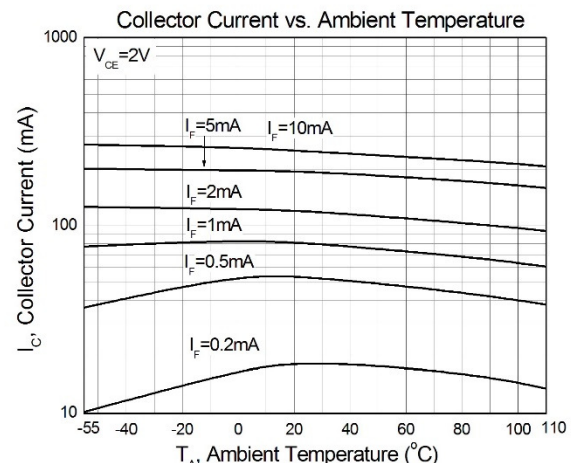


Figure 6

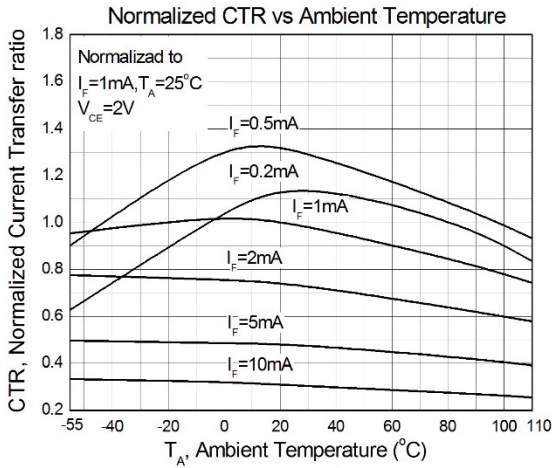


Figure 7

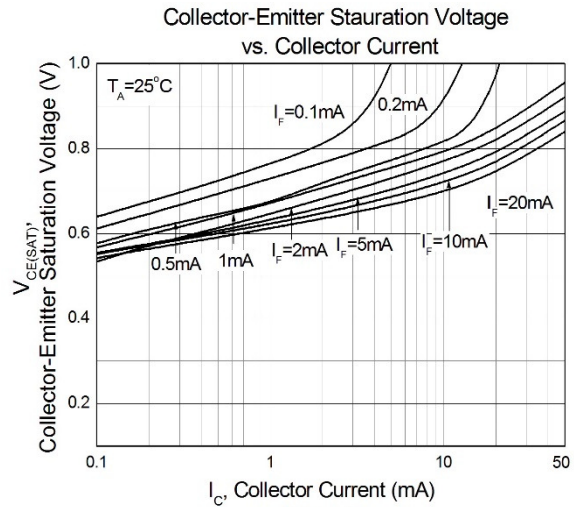


Figure 8

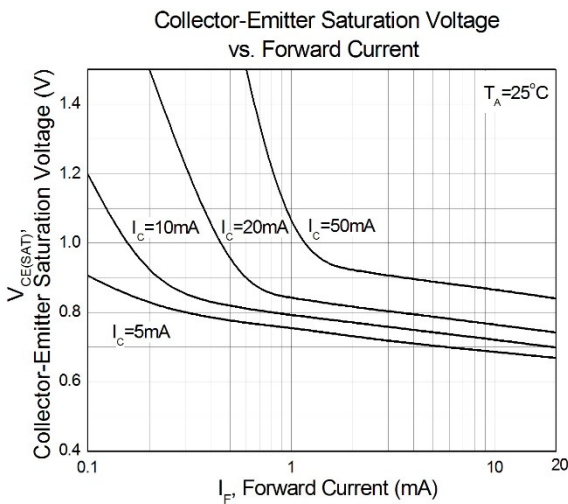


Figure 9

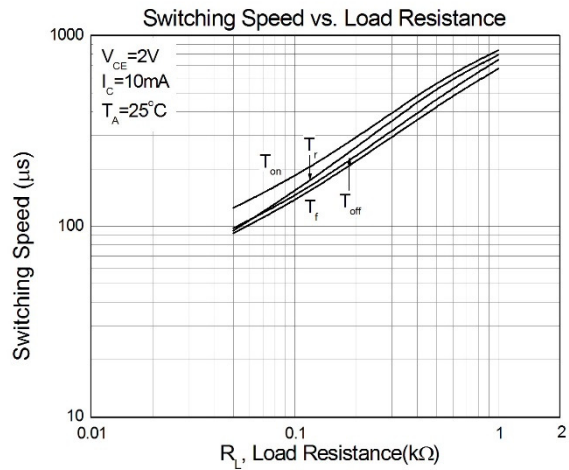


Figure 10

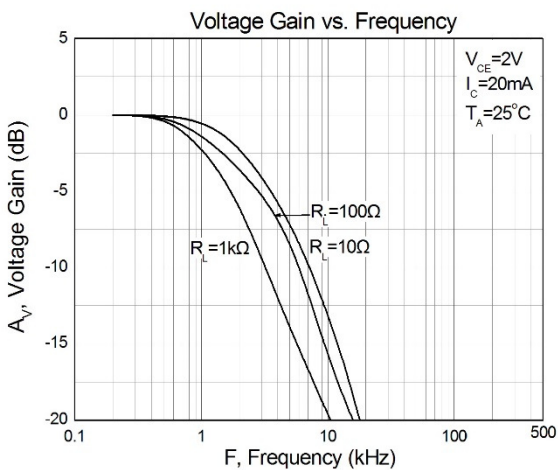


Figure 11

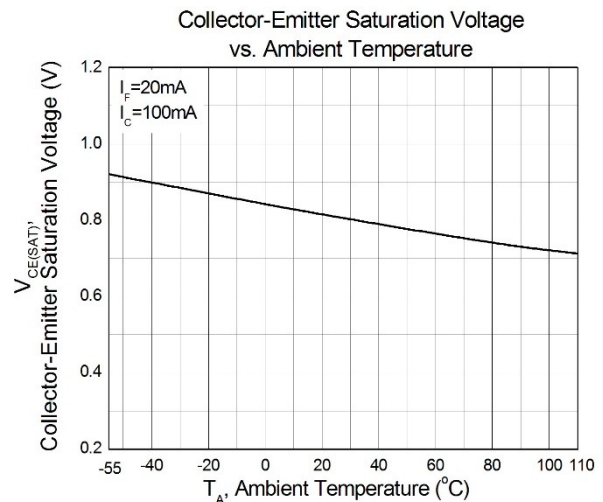
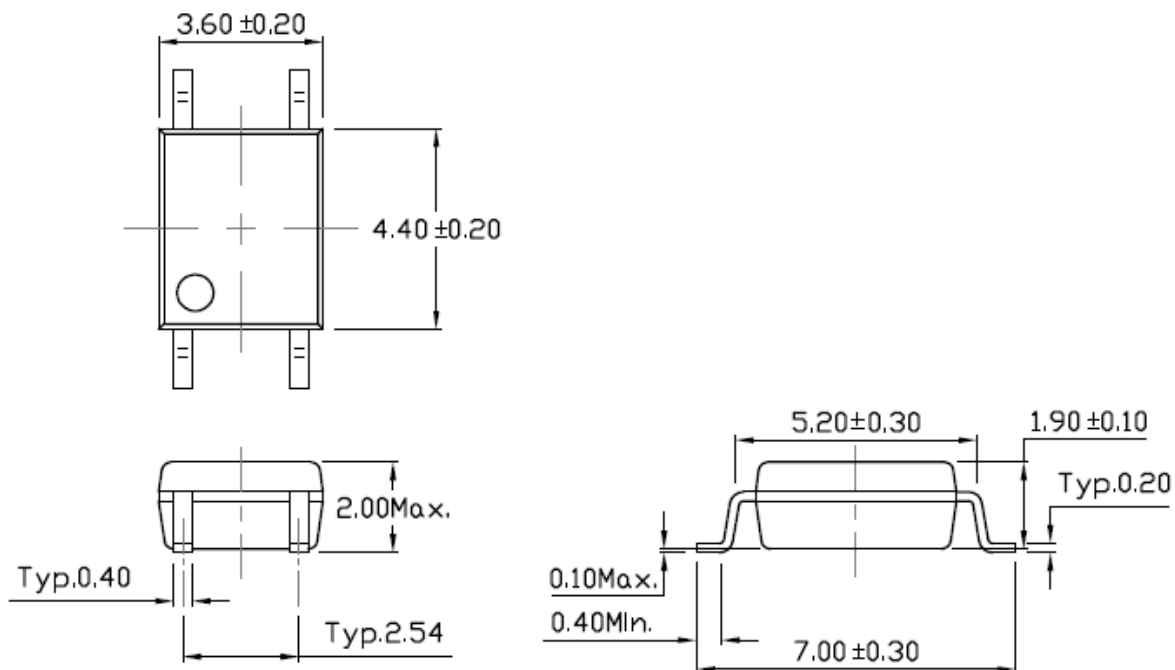


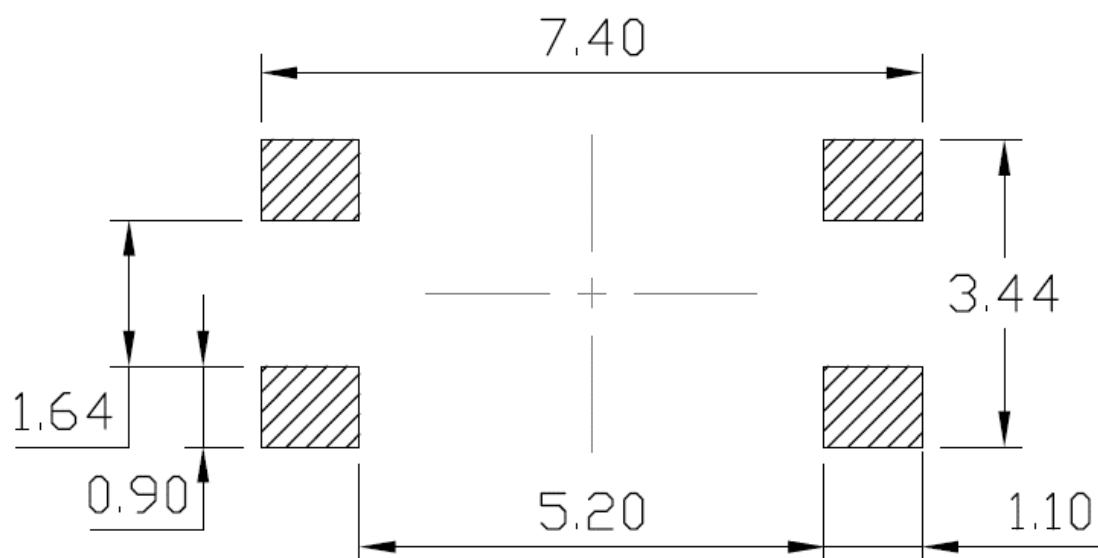
Figure 12



Package Dimension *Dimensions in mm unless otherwise stated*

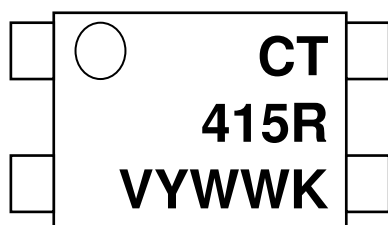


Recommended Solder Mask *Dimensions in mm unless otherwise stated*





Marking Information



Note:

- CT : Denotes “CT Micro”
- 415 : Product Number
- R : CTR Rank
- V : VDE Option
- Y : Fiscal Year
- WW : Work Week
- K : Manufacturing Code

Ordering Information

CT415X(V)(Z)

X = Part No. (X=A, B or None)

V = VDE option (V or none)

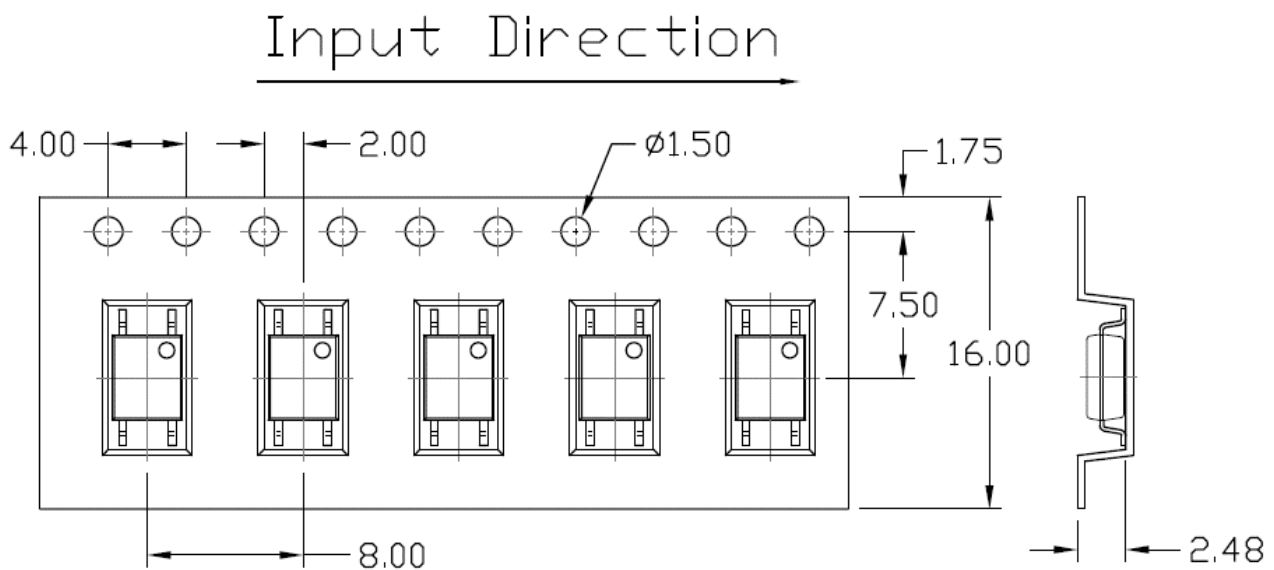
Z = Tape and reel option (T1, T2 or none)

Option	Description	Quantity
T1	Surface Mount Lead Forming – With Option 1 Taping	3000 Units/Reel
T2	Surface Mount Lead Forming – With Option 2 Taping	3000 Units/Reel

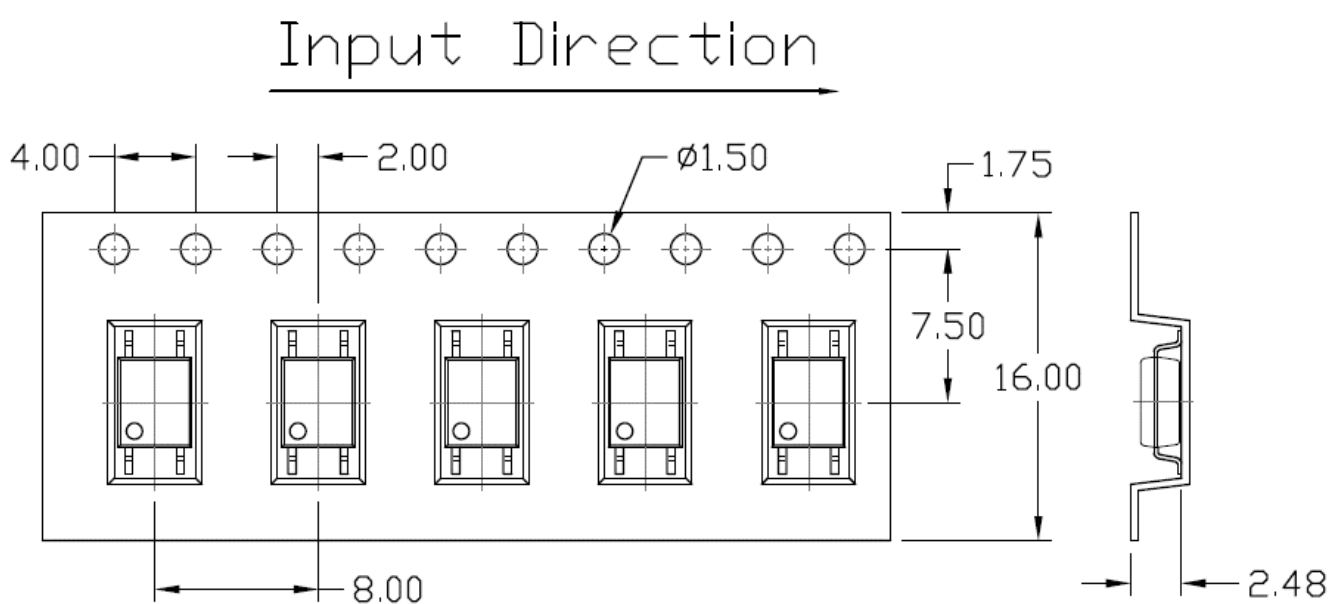


Carrier Tape Specifications *Dimensions in mm unless otherwise stated*

Option (T1)

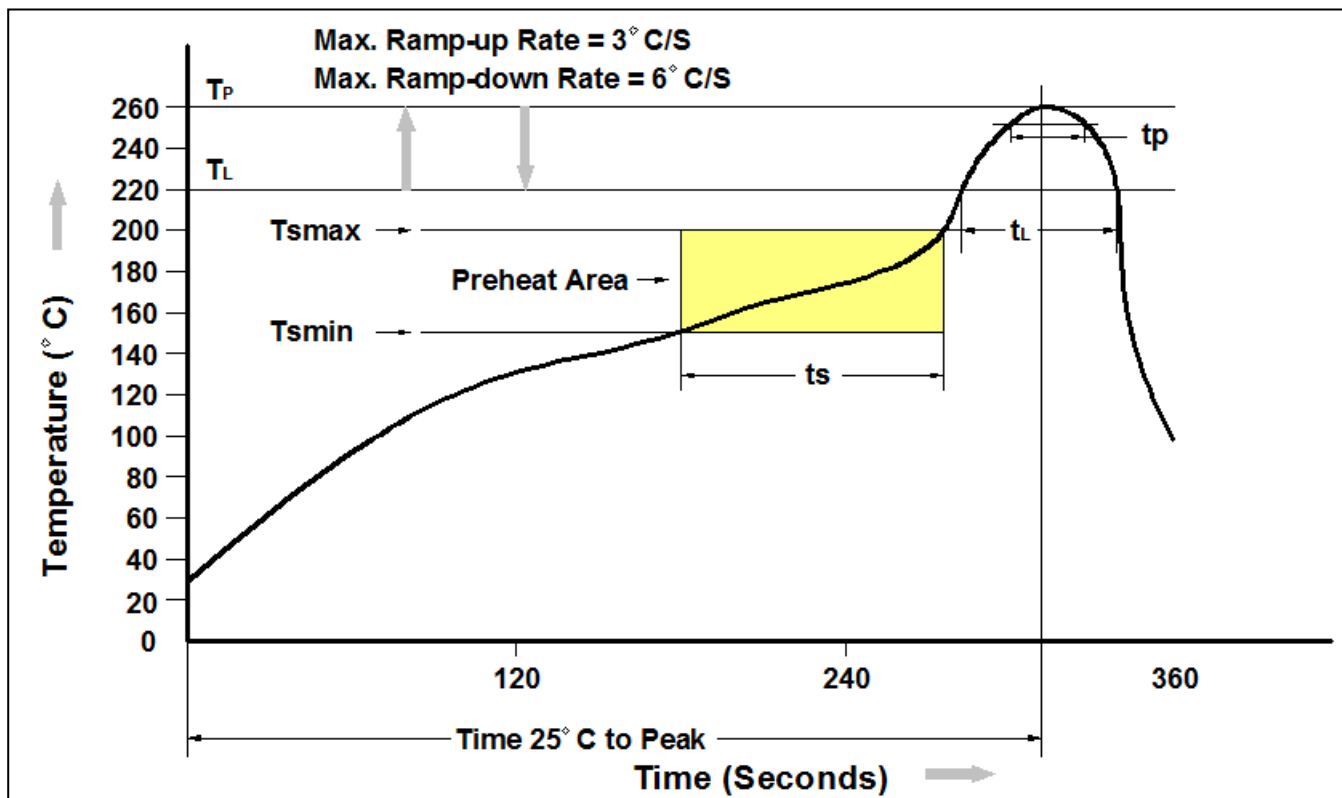


Option (T2)





Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150 °C
Temperature Max. (T _{smax})	200 °C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217 °C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Body Package Temperature	260 °C +0 °C / -5 °C
Time (t _P) within 5 °C of 260 °C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25 °C to Peak Temperature	8 minutes max.



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